

Silicon NPN Power Transistor

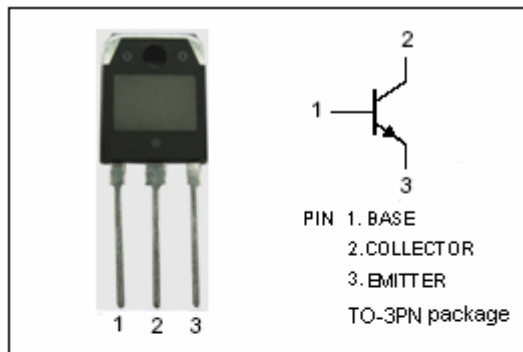
2SC3552

DESCRIPTION

- High Breakdown Voltage
- High Switching Speed
- Wide Area of Safe Operation

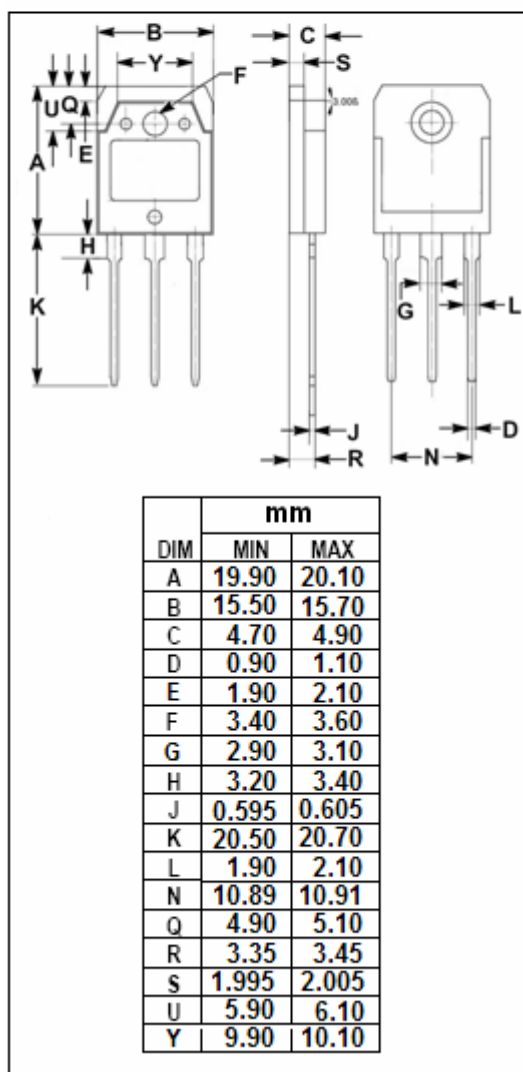
APPLICATIONS

- Designed for switching regulator applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1100	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current- Continuous	12	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current- Continuous	6	A
P_C	Collector Power Dissipation @ $T_C=25$	150	W
T_J	Junction Temperature	150	
T_{stg}	Storage Temperature Range	-55~150	



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ELECTRICAL CHARACTERISTICS

T_C=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 5mA; R _{BE} =	800			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	7			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	1100			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			2.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 800V ; I _E = 0			10	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V ; I _C = 0			10	μA
h _{FE-1}	DC Current Gain	I _C = 0.8A ; V _{CE} = 5V	10		40	
h _{FE-2}	DC Current Gain	I _C = 4A ; V _{CE} = 5V	8			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} =1.0MHz		215		pF
f _T	Current-Gain—Bandwidth Product	I _C = 0.8A ; V _{CE} = 10V		15		MHz

Switching Times

t _{on}	Turn-on Time	I _C = 8A , I _{B1} = 1.6A; I _{B2} = -3.2A R _L = 500 ; V _{CC} =400V			0.5	μs
t _{stg}	Storage Time				3.0	μs
t _f	Fall Time				0.3	μs

◆ **h_{FE-1} Classifications**

K	L	M
10-20	15-30	20-40